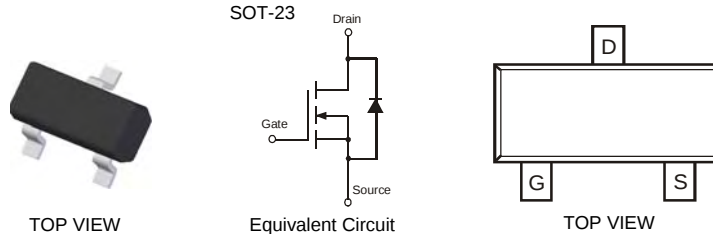


## Features

- Low On-Resistance
  - 53mΩ @V<sub>GS</sub> = 4.5V
  - 104mΩ @V<sub>GS</sub> = 2.5V
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Lead, Halogen and Antimony Free, RoHS Compliant (Note 1)**
- "Green" Device (Note 2)**
- Qualified to AEC-Q101 Standards for High Reliability**

## Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



## Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                | Symbol           | Value | Units |
|-------------------------------|------------------|-------|-------|
| Drain-Source Voltage          | V <sub>DSS</sub> | 20    | V     |
| Gate-Source Voltage           | V <sub>GSS</sub> | ±12   | V     |
| Drain Current (Note 3)        | I <sub>D</sub>   | 4.3   | A     |
| Pulsed Drain Current (Note 4) | I <sub>DM</sub>  | 15    | A     |

## Thermal Characteristics

| Characteristic                                   | Symbol                            | Value       | Units |
|--------------------------------------------------|-----------------------------------|-------------|-------|
| Total Power Dissipation (Note 3)                 | P <sub>D</sub>                    | 1.4         | W     |
| Thermal Resistance, Junction to Ambient (Note 3) | R <sub>θJA</sub>                  | 90          | °C/W  |
| Operating and Storage Temperature Range          | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C    |

## Electrical Characteristics @T<sub>A</sub> = 25°C unless otherwise specified

| Characteristic                      | Symbol              | Min  | Typ | Max  | Unit | Test Condition                                             |
|-------------------------------------|---------------------|------|-----|------|------|------------------------------------------------------------|
| <b>OFF CHARACTERISTICS (Note 5)</b> |                     |      |     |      |      |                                                            |
| Drain-Source Breakdown Voltage      | BV <sub>DSS</sub>   | 20   | —   | —    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA               |
| Zero Gate Voltage Drain Current     | I <sub>DSS</sub>    | —    | —   | 500  | nA   | V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V                |
| Gate-Source Leakage                 | I <sub>GSS</sub>    | —    | —   | ±100 | nA   | V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V               |
| <b>ON CHARACTERISTICS (Note 5)</b>  |                     |      |     |      |      |                                                            |
| Gate Threshold Voltage              | V <sub>GS(th)</sub> | 0.45 | —   | 1.4  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA |
| Static Drain-Source On-Resistance   | R <sub>DS(on)</sub> | —    | 42  | 53   | mΩ   | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 4.2A              |
|                                     |                     |      | 84  | 104  |      | V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 3.1A              |
| Forward Transfer Admittance         | Y <sub>fs</sub>     | —    | 6.6 | —    | S    | V <sub>DS</sub> = 5V, I <sub>D</sub> = 4.2A                |
| Diode Forward Voltage (Note 5)      | V <sub>SD</sub>     | —    | 0.7 | 1.2  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.0A                |
| <b>DYNAMIC CHARACTERISTICS</b>      |                     |      |     |      |      |                                                            |
| Input Capacitance                   | C <sub>iss</sub>    | —    | 325 | —    | pF   | V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V<br>f = 1.0MHz  |
| Output Capacitance                  | C <sub>oss</sub>    | —    | 92  | —    | pF   |                                                            |
| Reverse Transfer Capacitance        | C <sub>rss</sub>    | —    | 70  | —    | pF   |                                                            |

- Notes:
- No purposefully added lead. Halogen and Antimony Free.
  - Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  - Device mounted on FR-4 PCB, on 2oz Copper pad layout with R<sub>θJA</sub> = 90°C/W.
  - Repetitive rating, pulse width limited by junction temperature.
  - Short duration pulse test used to minimize self-heating effect.

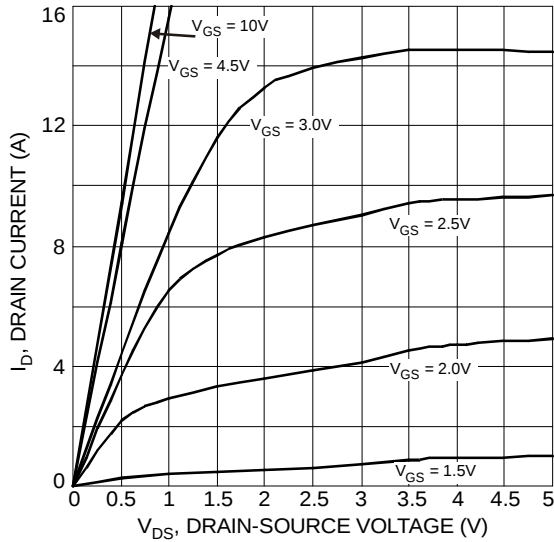


Fig. 1 Typical Output Characteristic

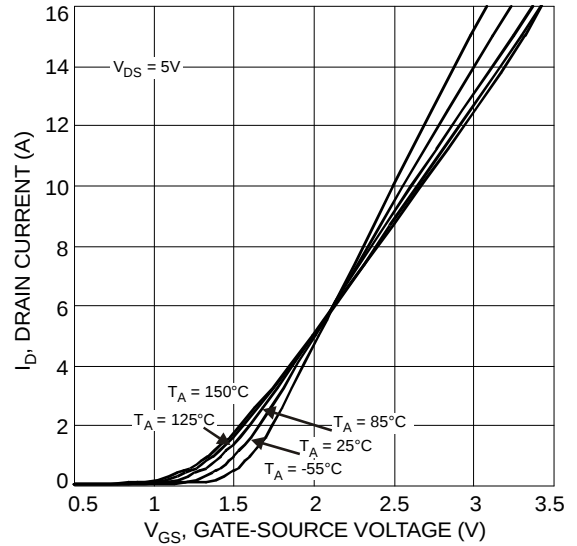


Fig. 2 Typical Transfer Characteristic

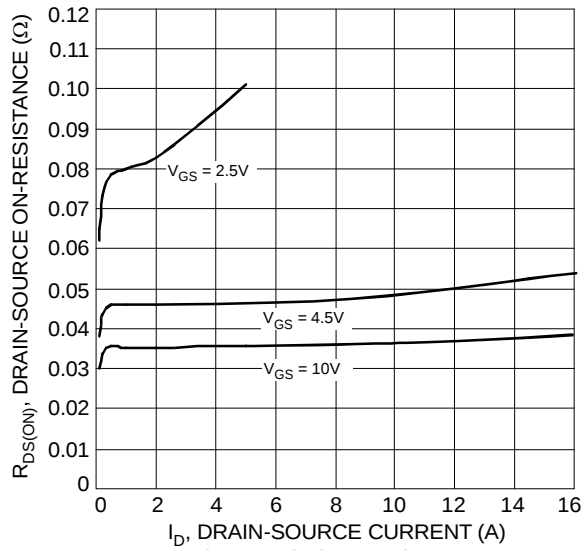


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

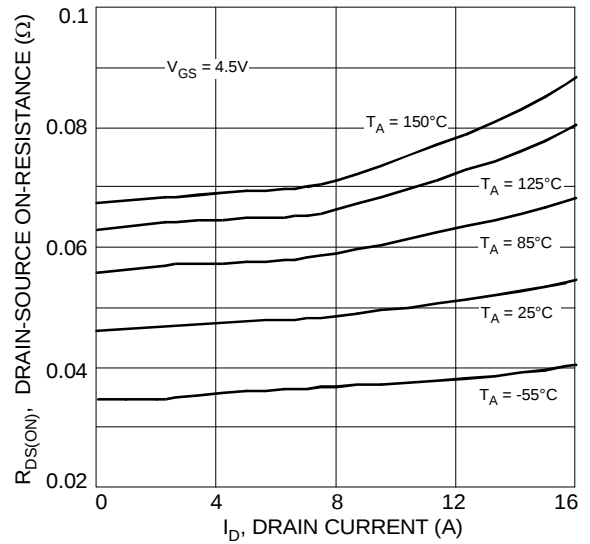


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

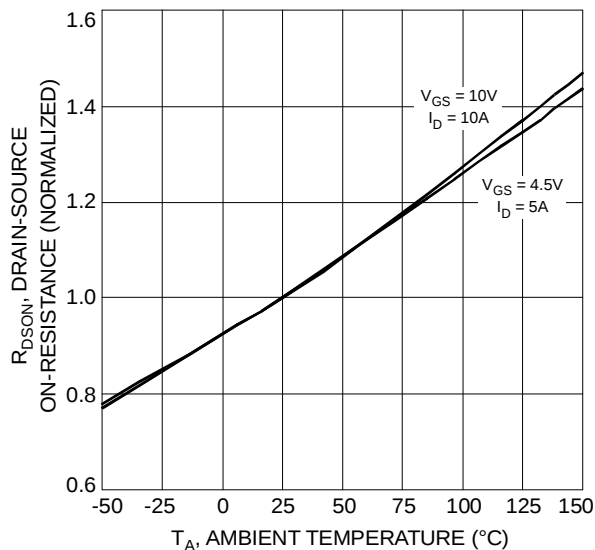


Fig. 5 On-Resistance Variation with Temperature

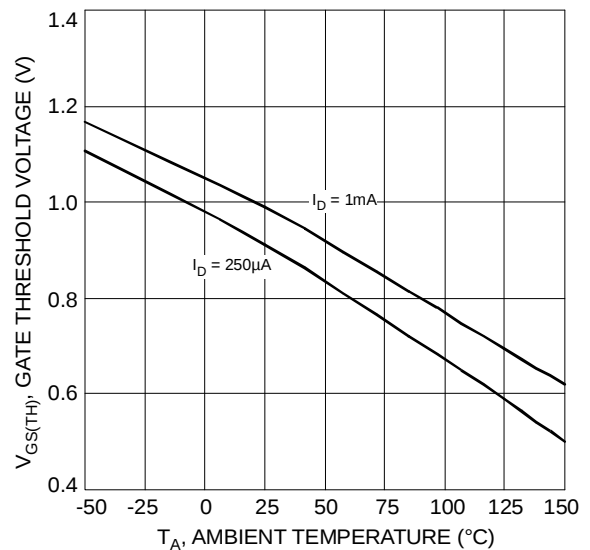


Fig. 6 Gate Threshold Variation vs. Ambient Temperature

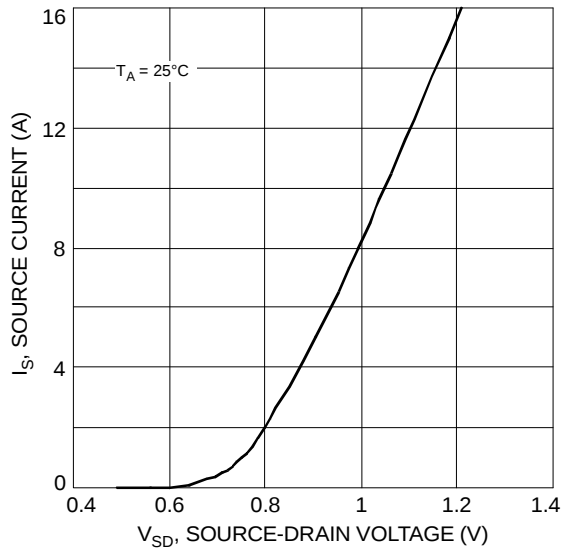


Fig. 7 Diode Forward Voltage vs. Current

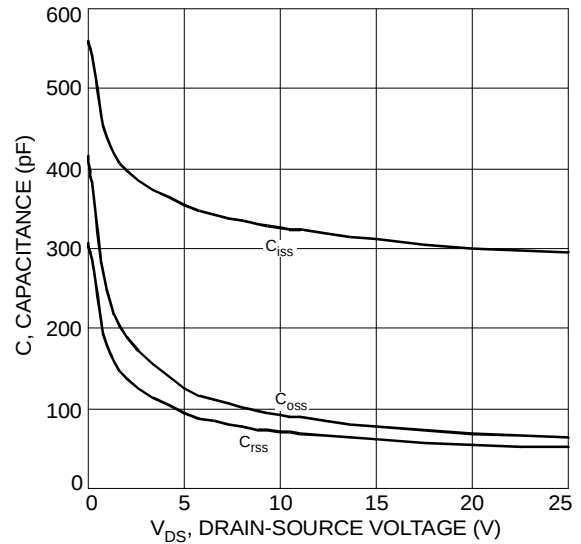


Fig. 8 Typical Total Capacitance

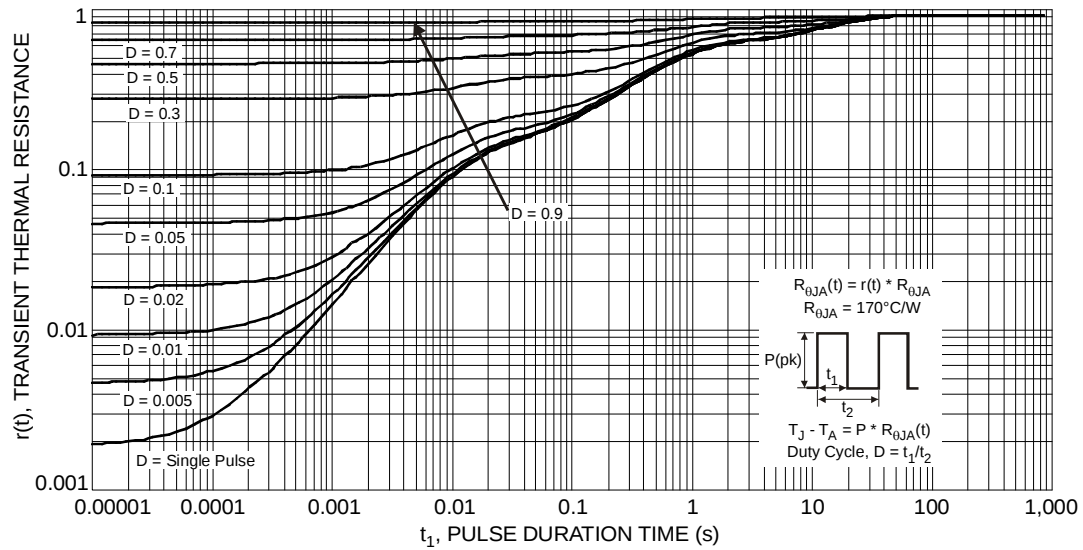


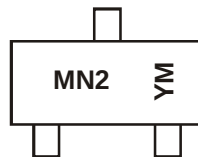
Fig. 9 Transient Thermal Response

## Ordering Information (Note 7)

| Part Number | Case   | Packaging        |
|-------------|--------|------------------|
| DMN2104L-7  | SOT-23 | 3000/Tape & Reel |

 Notes: 7. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

## Marking Information



MN2 = Marking Code  
 YM = Date Code Marking  
 Y = Year (ex: V = 2008)  
 M = Month (ex: 9 = September)

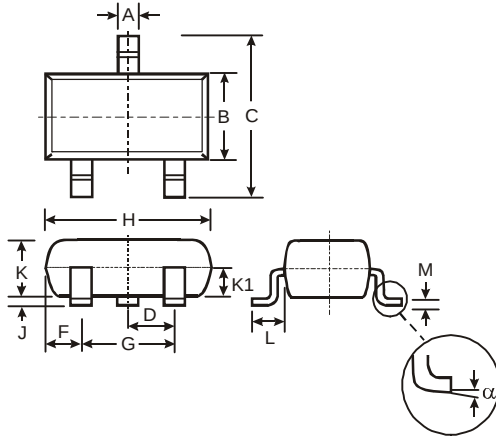
### Date Code Key

| Year | 2008 | 2009 | 2010 | 2011 | 2012 | 2013 | 2014 | 2015 |
|------|------|------|------|------|------|------|------|------|
| Code | V    | W    | X    | Y    | Z    | A    | B    | C    |

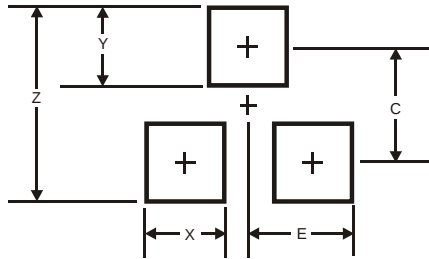
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
|-------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Code  | 1   | 2   | 3   | 4   | 5   | 6   | 7   | 8   | 9   | O   | N   | D   |

## Package Outline Dimensions



| SOT-23               |       |      |       |
|----------------------|-------|------|-------|
| Dim                  | Min   | Max  | Typ   |
| A                    | 0.37  | 0.51 | 0.40  |
| B                    | 1.20  | 1.40 | 1.30  |
| C                    | 2.30  | 2.50 | 2.40  |
| D                    | 0.89  | 1.03 | 0.915 |
| F                    | 0.45  | 0.60 | 0.535 |
| G                    | 1.78  | 2.05 | 1.83  |
| H                    | 2.80  | 3.00 | 2.90  |
| J                    | 0.013 | 0.10 | 0.05  |
| K                    | 0.903 | 1.10 | 1.00  |
| K1                   | -     | -    | 0.400 |
| L                    | 0.45  | 0.61 | 0.55  |
| M                    | 0.085 | 0.18 | 0.11  |
| $\alpha$             | 0°    | 8°   | -     |
| All Dimensions in mm |       |      |       |

## Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z          | 2.9           |
| X          | 0.8           |
| Y          | 0.9           |
| C          | 2.0           |
| E          | 1.35          |

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